Nch 30V 3.5A Power MOSFET

V _{DSS}	30V
R _{DS(on)} (Max.)	37mΩ
I _D	±3.5A
P _D	1W

Features

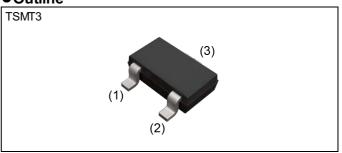
- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT3).
- 4) Pb-free lead plating; RoHS compliant

Application

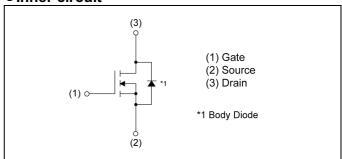
Switching

● Absolute maximum ratings (I _a = 25°C)					
Symbol	Value	Unit			
V_{DSS}	30	V			
I _D *1	±3.5	А			
I _{D,pulse} *2	±12	А			
V_{GSS}	±20	V			
E _{AS} *3	1.9	mJ			
I _{AS} *3	3.5	Α			
P _D *4	1	W			
T _j	150	°C			
T _{stg}	-55 to +150	°C			
	V _{DSS} I _D *1 I _{D,pulse} *2 V _{GSS} E _{AS} *3 I _{AS} *3 P _D *4 T _j	$\begin{array}{c ccccc} V_{DSS} & 30 & & & \\ & I_{D}^{*1} & \pm 3.5 & & \\ & I_{D,pulse}^{*2} & \pm 12 & & \\ & V_{GSS} & \pm 20 & & \\ & E_{AS}^{*3} & 1.9 & & \\ & I_{AS}^{*3} & 3.5 & & \\ & P_{D}^{*4} & 1 & & \\ & T_{j} & 150 & & \\ \end{array}$			

Outline



•Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	180
Туре	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TCL
	Marking	ZS

●Thermal resistance

Parameter	Symbol	Values			Unit
Parameter	Symbol	Min.	Тур.	Max.	Uniit
Thermal resistance, junction - ambient	R _{thJA} *4	-	125	-	°C/W

● Electrical characteristics (T_a = 25°C)

Davamatav	Cymahal	Conditions		Values		Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 1mA$	30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I _D = 1mA referenced to 25°C	-	20.84	-	mV/°C
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 1mA$	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\DeltaV_{GS(th)}}{\DeltaT_j}$	I _D = 1mA referenced to 25°C	-	-3.25	-	mV/°C
Static drain - source	D *5	V _{GS} = 10V, I _D = 3.5A	-	28	37	m0
on - state resistance	R _{DS(on)} *5	V _{GS} = 4.5V, I _D = 3.5A	-	43	56	mΩ
Gate input resistance	R _G		-	2.8	-	Ω
Transconductance	9 _{fs} *5	$V_{DS} = 5V, I_{D} = 3.5A$	2.4	-	-	S

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10µs, Duty cycle \leq 1%

^{*3} L \simeq 200 μ H, V_{DD} = 15V, R_G = 25 Ω , STARTING T_{ch} = 25 $^{\circ}$ C Fig.3-1,3-2

^{*4} Mounted on a ceramic boad (30×30×0.8mm)

^{*5} Pulsed

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	V _{GS} = 0V	-	250	-	
Output capacitance	C _{oss}	V _{DS} = 15V	-	40	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	1	35	1	
Turn - on delay time	$t_{d(on)}^{*5}$	V _{DD} ≈ 15V,V _{GS} = 10V	-	5.5	1	
Rise time	t _r *5	I _D = 1.75A	-	7.5	-	no
Turn - off delay time	t _{d(off)} *5	$R_L = 8.6\Omega$		10	-	ns
Fall time	t _f *5	$R_G = 10\Omega$	-	3.5	-	

• Gate charge characteristics $(T_a = 25^{\circ}C)$

Davamatav	Cymah al	Conditi			Values		Unit
Parameter	Symbol Conditions		Min.	Тур.	Max.	Offic	
Total gate charge	○ *5		V _{GS} = 10V	-	6.0	-	
Total gate charge	Q_g^{*5}	V _{DD} ≈ 15V	-	3.1	-	0	
Gate - Source charge	Q _{gs} *5	I _D = 4.5A	V _{GS} = 4.5V	-	1.2	-	nC
Gate - Drain charge	Q _{gd} *5			-	1.1	-	

● Body diode electirical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions		Values	_	Unit
	Symbol	Conditions	Min.	Тур.	Max.	Offic
Body diode continuous forward current	I _S *1	T - 25°C	-	1	0.8	^
Body diode pulse current	I _{SP} *2	T _a = 25°C	-	-	12	A
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_S = 0.8A$	-	-	1.2	V

Fig.1 Typical Output Characteristics(I)

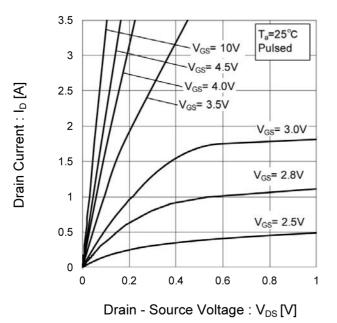
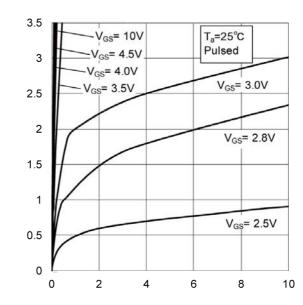


Fig.2 Typical Output Characteristics(II)

Drain Current : I_D [A]



Drain - Source Voltage : V_{DS} [V]

Fig.3 Breakdown Voltage vs. Junction Temperature

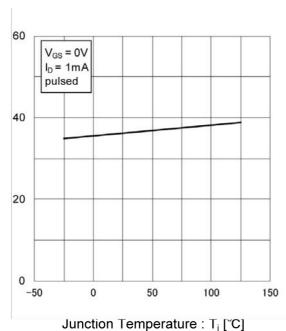


Fig.4 Typical Transfer Characteristics

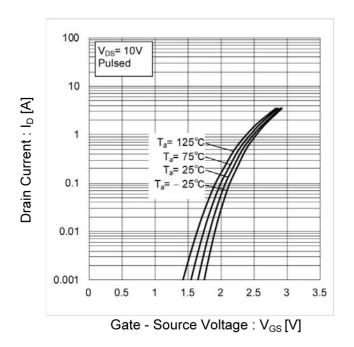
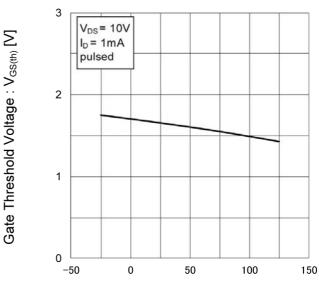


Fig.5 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.6 Transconductance vs. Drain Current

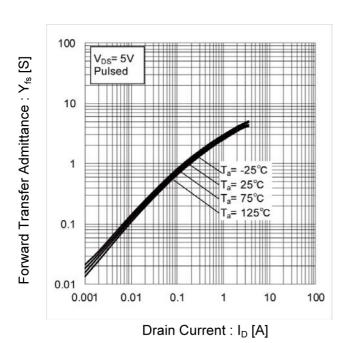


Fig.7 Drain Current Derating Curve

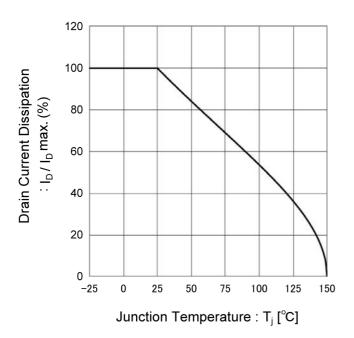


Fig.8 Static Drain - Source On - State Resistance vs. Gate Source Voltage

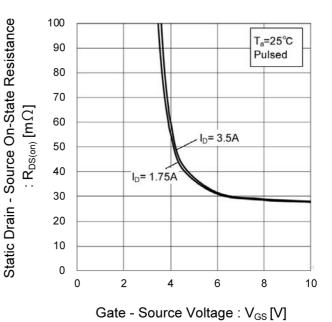
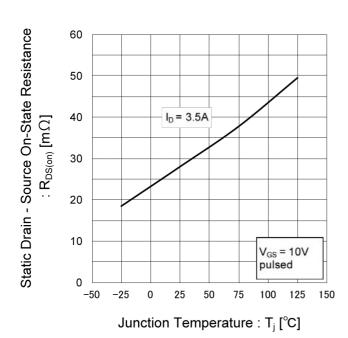


Fig.9 Static Drain - Source On - State Resistance vs. Junction Temperature



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RQ5E035BN

• Electrical characteristic curves

Fig.10 Static Drain - Source On - State Resistance vs. Drain Current(I)

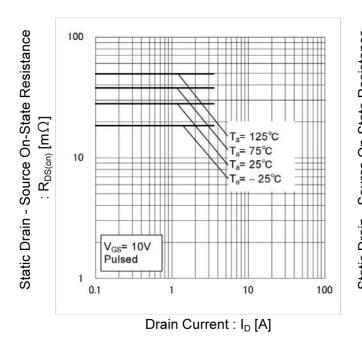
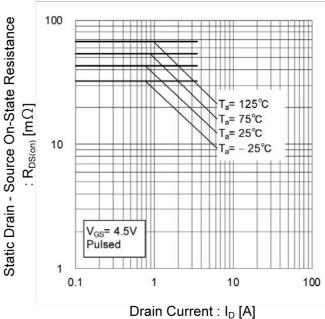


Fig.11 Static Drain - Source On - State Resistance vs. Drain Current(II)



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Fig.12 Typical Capacitance vs. Drain - Source Voltage

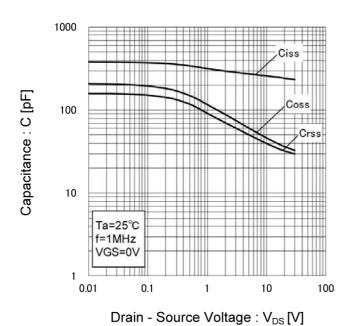
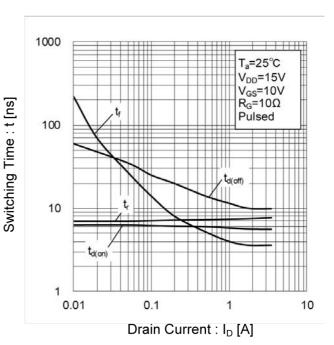


Fig.13 Switching Characteristics



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Fig.14 Dynamic Input Characteristics

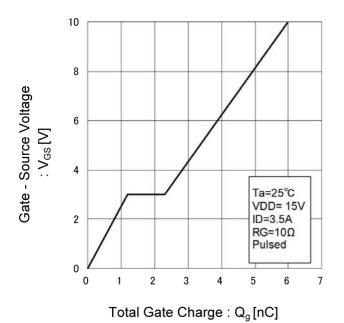
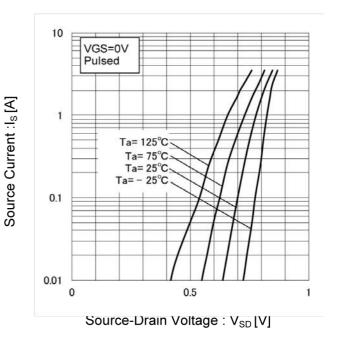


Fig.15 Source Current vs. Source Drain Voltage



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Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

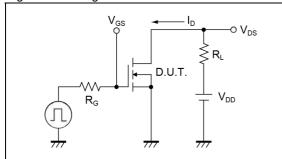


Fig.2-1 Gate Charge Measurement Circuit

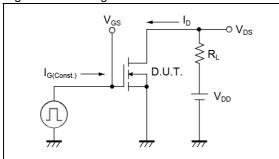


Fig.3-1 AVALANCHE MEASUREMENT CIRCUIT

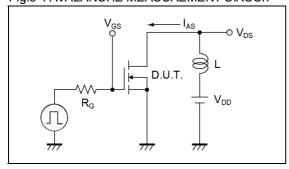


Fig.1-2 Switching Waveforms

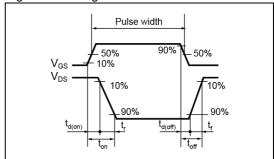


Fig.2-2 Gate Charge Waveform

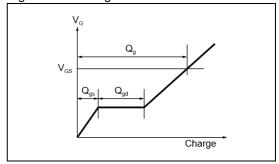
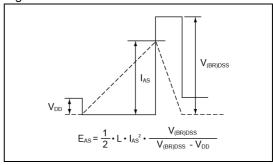
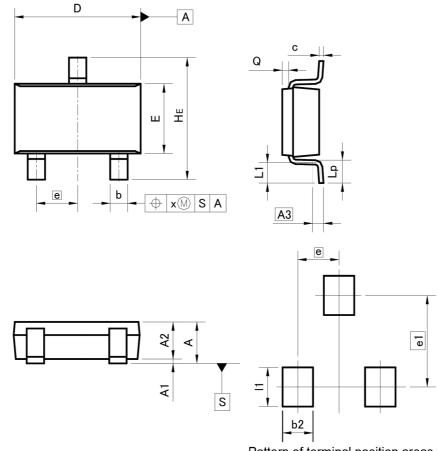


Fig.3-2 AVALANCHE WAVEFORM



Dimensions

TSMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM -	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	-	1.00	-	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.	25	0.0	10
b	0.35	0.50	0.014	0.020
С	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.	95	0.0	37
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
x	_	0.20	-	0.008

DIM -	MILIM	MILIMETERS		HES
DIN	MIN	MAX	MIN	MAX
b2		0.70	1=	0.028
e1	2.	10	0.0	083
11	-	0.90	-	0.035

Dimension in mm/inches



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